Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method for depositing a material on a substrate wafer having the following method steps:

(a) providing the substrate wafer, which has a growth area intended for a later material deposition;

(b) ~~applying~~ affixing a thermal radiation absorption layer, which exhibits a good absorption of thermal radiation, on a rear side of the substrate wafer which faces away from the growth area;

(c) heating the substrate wafer to a deposition temperature;

(d) depositing a material onto the growth area of the substrate wafer by an MOVPE method;

wherein the thermal radiation absorption layer is ~~applied~~ affixed to the substrate before the deposition of the material onto the growth area of the substrate wafer; and

wherein the substrate wafer is heated by the thermal radiation absorption layer during MOVPE.

2. (Currently Amended) The method according to ~~Claim~~ claim 1, in which the deposited material is a semiconductor material.

3. (Currently Amended) The method according to ~~Claim~~ claim 1, in which the

deposited material comprises at least one layer made of $Al_xGa_yIn_{1-x-y}N$, where $0 \leq x+y \leq 1$, $0 \leq x \leq 1$, $0 \leq y \leq 1$ apply.

4. (Previously Presented) The method according to claim 1, in which a substrate wafer is used which essentially comprises SiC or an SiC-based material.

5. (Currently Amended) The method according to claim 1, in which a material or a material mixture which exhibits inert ~~behaviour~~ behavior during the deposition method in accordance with method step (d) is ~~applied~~ affixed to the substrate as the thermal radiation absorption layer.

6. (Currently Amended) The method according to claim 1, in which a material or a material mixture which is compatible with a material and/or a contact-connecting process of an electrical contact that is to be applied later, is ~~applied~~ affixed to the substrate as the thermal radiation absorption layer.

7. (Currently Amended) The method according to claim 1, in which the thermal radiation absorption layer is ~~applied~~ affixed to the substrate by means of sputtering in accordance with method step (b).

8. (Previously Presented) The method according to claim 1, in which a doped Si layer, in particular a highly doped Si layer, is used as the thermal radiation absorption layer.

9. (Currently Amended) The method according to ~~Claim~~ claim 8, in which the Si layer is ~~applied~~ affixed to the substrate with a thickness which lies between 10 nm and 20 μm inclusive.

10. (Currently Amended) The method according to ~~Claim~~ claim 8, in which the Si layer has a doping of at least $1 \times 10^{19}/cm^3$.

11. (Previously Presented) The method according to claim 1, in which the heating in accordance with method step (c) is essentially effected by means of thermal radiation.

12. (Previously Presented) The method according to claim 1, in which, in method step (c), a heating source is used which generates thermal radiation of a spectral range for which the thermal radiation absorption layer exhibits good radiation absorption.

13. (Previously Presented) The method according to claim 1, in which a non-metallic layer is used as the thermal radiation absorption layer.

14. (New) The method according to claim 1, in which a contact metalization is applied to the rear side of the substrate wafer, the thermal radiation absorption layer being affixed to the contact metalization.

15. (New) The method according to claim 14, in which the thermal radiation absorption layer comprises highly doped silicone.